**Product data sheet** 

### 1. General description

Planar passivated high commutation three quadrant triac in a SOT54 (TO-92) plastic package. This "series ER" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers. It has reverse pinning to that of the standard triac in this package.

#### 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High commutation capability with sensitive gate
- High immunity to false turn-on by dV/dt
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Reverse pinning version (ER)
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

# 3. Applications

- General purpose motor control
- Small loads in washing machines
- · Solenoid drivers

#### 4. Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter                                | Conditions   | Min | Тур | Max  | Unit |
|---------------------|--|--|-----|-----|------|------|
| $V_{DRM}$           | repetitive peak off-<br>state voltage    |  | -   | -   | 800  | V    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5      | -   | -   | 12.5 | А    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; T <sub>lead</sub> ≤ 54 °C; <u>Fig. 1</u> ;<br><u>Fig. 2</u> ; <u>Fig. 3</u>    | -   | -   | 1    | А    |
| Static characte     | eristics                                 |  |     |     |      |      |
| I <sub>GT</sub>     | gate trigger current                     | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$<br>$T_j = 25 \text{ °C; } Fig. 7$ | 1   | -   | 10   | mA   |





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| Symbol | Parameter | Conditions   | Min | Тур | Max | Unit |
|--------|-----------|--|-----|-----|-----|------|
|        |           | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$<br>$T_j = 25 \text{ °C}; Fig. 7$                | 1   | -   | 10  | mA   |
|        |           | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$ | 1   | -   | 10  | mA   |

# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description     | Simplified outline                           | Graphic symbol |
|-----|--------|-----------------|--|----------------|
| 1   | T1     | main terminal 1 |  | T2—T1          |
| 2   | G      | gate            | <u>                                     </u> | sym051         |
| 3   | T2     | main terminal 2 |  |                |

# 6. Ordering information

Table 3. Ordering information

| Type number  | Package |   |         |  |  |  |
|--------------|---------|---|---------|--|--|--|
|              | Name    | Description   | Version |  |  |  |
| BTA201-800ER | TO-92   | plastic single-ended leaded (through hole) package; 3 leads | SOT54   |  |  |  |

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                            | Conditions  | Min | Max  | Unit             |
|---------------------|--------------------------------------|---|-----|------|------------------|
| $V_{DRM}$           | repetitive peak off-state voltage    |   | -   | 800  | V                |
| I <sub>T(RMS)</sub> | RMS on-state current                 | full sine wave; T <sub>lead</sub> ≤ 54 °C; <u>Fig. 1</u> ;<br><u>Fig. 2</u> ; <u>Fig. 3</u> | -   | 1    | Α                |
| I <sub>TSM</sub>    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ;<br>$t_p = 16.8  \text{ms}$                   | -   | 13.7 | А                |
|                     |                                      | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5   | -   | 12.5 | А                |
| l <sup>2</sup> t    | I <sup>2</sup> t for fusing          | t <sub>p</sub> = 10 ms; SIN   | -   | 0.78 | A <sup>2</sup> s |
| dl <sub>T</sub> /dt | rate of rise of on-state current     | $I_T$ 1.5 A; $I_G$ 0.2 A; $dI_G/dt = 0.2$ A/ $\mu$ s  | -   | 100  | A/µs             |
| I <sub>GM</sub>     | peak gate current                    |   | -   | 2    | Α                |
| P <sub>GM</sub>     | peak gate power                      |   | -   | 5    | W                |
| P <sub>G(AV)</sub>  | average gate power                   | over any 20 ms period   | -   | 0.1  | W                |
| Tj                  | junction temperature                 |   | -40 | 125  | °C               |

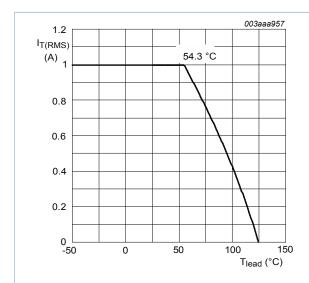


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

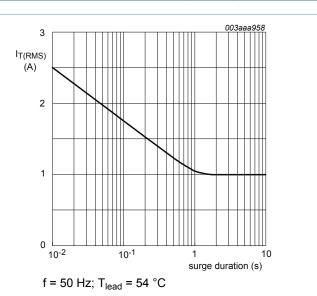


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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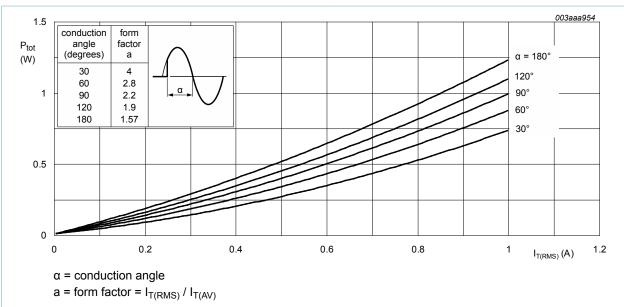
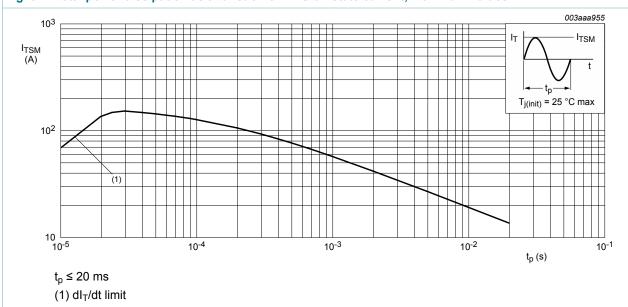


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



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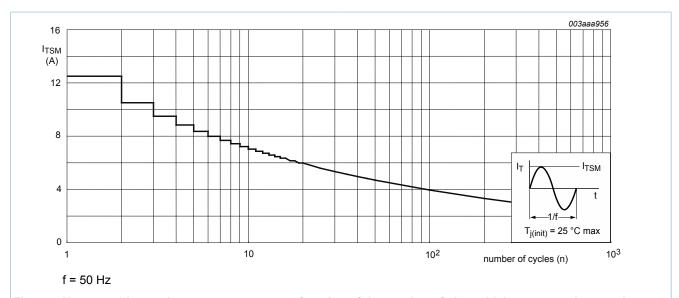
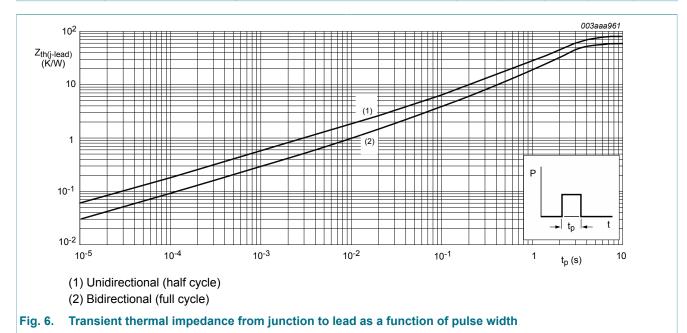


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

### 8. Thermal characteristics

Table 5. Thermal characteristics

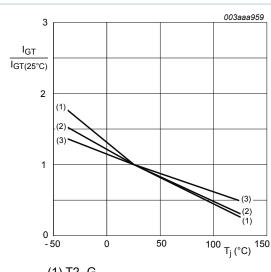
| Symbol                  | Parameter   | Conditions         | Min | Тур | Max | Unit |
|-------------------------|---|--------------------|-----|-----|-----|------|
| R <sub>th(j-lead)</sub> | thermal resistance from junction to lead          | full cycle; Fig. 6 | -   | -   | 60  | K/W  |
|                         |   | half cycle; Fig. 6 | -   | -   | 80  | K/W  |
| R <sub>th(j-a)</sub>    | thermal resistance<br>from junction to<br>ambient |                    | -   | 150 | -   | K/W  |



## 9. Characteristics

Table 6. Characteristics

| Symbol                | Parameter                             | Conditions  | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|---|-----|-----|-----|------|
| Static char           | acteristics                           |   |     |     |     |      |
| I <sub>GT</sub>       | gate trigger current                  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$<br>$T_j = 25 \text{ °C; } Fig. 7$                                | 1   | -   | 10  | mA   |
|                       |                                       | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$<br>$T_j = 25 \text{ °C; } Fig. 7$                               | 1   | -   | 10  | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$<br>$T_j = 25 \text{ °C}; Fig. 7$                            | 1   | -   | 10  | mA   |
| IL                    | latching current                      | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 8$                                   | -   | -   | 12  | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$<br>$T_j = 25 \text{ °C}; Fig. 8$                                   | -   | -   | 20  | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$             | -   | -   | 12  | mA   |
| I <sub>H</sub>        | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>  | -   | -   | 12  | mA   |
| V <sub>T</sub>        | on-state voltage                      | I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>  | -   | 1.2 | 1.5 | V    |
| $V_{GT}$              | gate trigger voltage                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$<br>Fig. 11  | -   | 0.7 | 1   | V    |
|                       |                                       | V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C;<br>Fig. 11                                   | 0.2 | 0.3 | -   | V    |
| I <sub>D</sub>        | off-state current                     | V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C   | -   | 0.1 | 0.5 | mA   |
| Dynamic cl            | haracteristics                        |   | ,   |     |     |      |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 12   | 600 | -   | -   | V/µs |
| dl <sub>com</sub> /dt | rate of change of commutating current | $V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 1 A; $dV_{com}/dt$ = 20 V/s; (snubberless condition); gate open circuit | 2.5 | -   | -   | A/ms |
|                       |                                       | $V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 1 A;<br>$dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit                | 3.5 | -   | -   | A/ms |



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

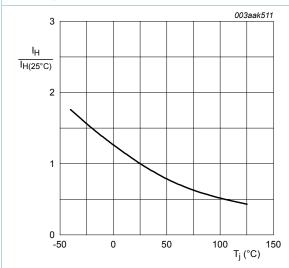


Fig. 9. Normalized holding current as a function of junction temperature

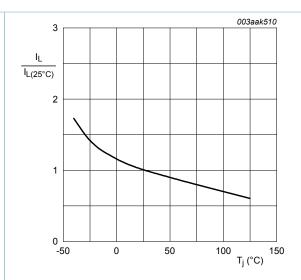
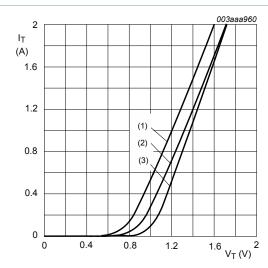


Fig. 8. Normalized latching current as a function of junction temperature

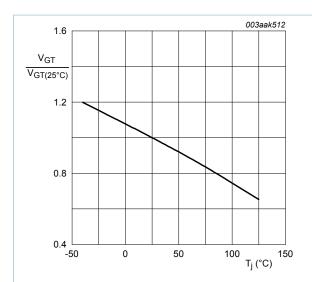


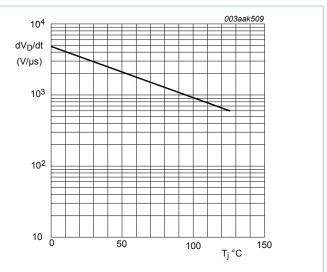
- $V_o$  = 1.02 V;  $R_s$  = 0.358  $\Omega$
- (1)  $T_j$  = 125 °C; typical values
- (2) T<sub>i</sub> = 125 °C; maximum values
- (3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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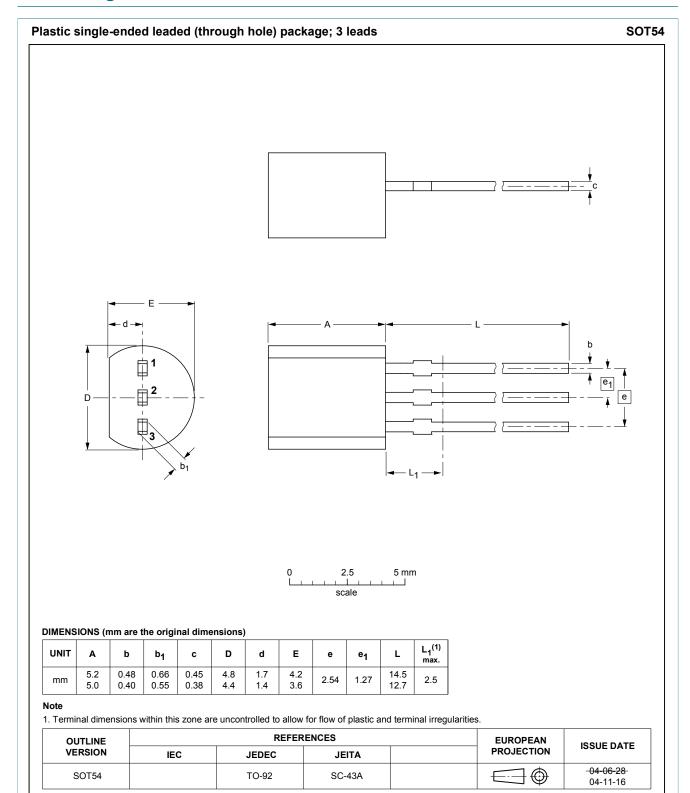


junction temperature

Fig. 11. Normalized gate trigger voltage as a function of Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

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# 10. Package outline



### Fig. 13. Package outline TO-92 (SOT54)

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